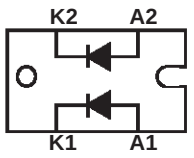
STTA3006P/PI
STTA6006TV1/2

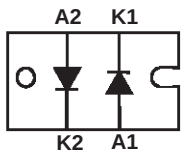
TURBOSWITCH ™ ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCT CHARACTERISTICS

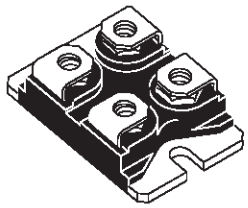
$I_{F(AV)}$	30A / 2 x 30A
V_{RRM}	600V
t_{rr} (typ)	35ns
V_F (max)	1.5V



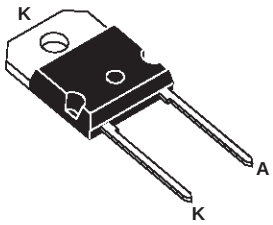
STTA6006TV1



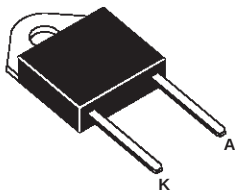
STTA6006TV2



ISOTOP™



SOD93
STTA3006P



DOP3I
STTA3006PI

FEATURES AND BENEFITS

- SPECIFICTO "FREEWHEEL MODE" OPERATIONS: FREEWHEEL OR BOOSTER DIODE
- ULTRA-FAST AND SOFT RECOVERY
- VERY LOW OVERALL POWER LOSSES IN BOTH THE DIODE AND THE COMPANION TRANSISTOR
- HIGH FREQUENCY OPERATIONS
- INSULATED PACKAGE : ISOTOP & DOP3I
  Electrical insulation : 2500V_{RMS}
  Capacitance < 12 pF (DOP3I)
  Capacitance < 45 pF (ISOTOP)

DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast high voltage power diodes from 600V to 1200V.
TURBOSWITCH family, drastically cuts losses in both the diode and the associated switching IGBT or MOSFET in all "freewheel mode" operations and is particularly suitable and efficient in motor control freewheel applications and in booster diode applications in power factor control circuitries.
Packaged either in ISOTOP, DOP3I or SOD93 these 600V devices are particularly intended for use on 240V domestic mains.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
V_{RSM}	Non repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward current		50	A
I_{FRM}	Repetitive peak forward current	tp=5µs F=5kHz square	300	A
I_{FSM}	Surge non repetitive forward current	tp=10 ms sinusoidal	230	A
T_j	Maximum operating junction temperature		150	°C
T_{stg}	Storage temperature range		-65 to 150	°C

TM : TURBOSWITCH is a trademark of STMicroelectronics

THERMAL AND POWER DATA (Per diode)

Symbol	Parameter	Test conditions		Value	Unit
$R_{th(j-c)}$	Junction to case thermal resistance	ISOTOP	Per diode	1.4	°C/W
			Total	0.75	
		DOP3I		1.8	
		SOD93		1.2	
$R_{th(c)}$		ISOTOP	Coupling	0.1	°C/W
P_1	Conduction power dissipation $I_{F(AV)}$ = 30A δ =0.5	ISOTOP	Tc= 74°C	54	W
		DOP3I	Tc= 52°C		
		SOD93	Tc= 85°C		
P_{max}	Total power dissipation Pmax = P1 + P3 (P3 = 10% P1)	ISOTOP	Tc= 66°C	60	W
		DOP3I	Tc= 42°C		
		SOD93	Tc= 78°C		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions		Min	Typ	Max	Unit
V_F *	Forward voltage drop	I_F =30A	Tj = 25°C Tj = 125°C		 1.25	1.75 1.5	V V
I_R **	Reverse leakage current	V_R =0.8 × V_{RRM}	Tj = 25°C Tj = 125°C		 3	150 8	µA mA
V_{to}	Threshold voltage	Ip < 3.I_{AV}	Tj = 125°C			1.15	V
rd	Dynamic resistance					11	mΩ

Test pulses : * tp = 380 µs, δ < 2%
** tp = 5 ms, δ < 2%

To evaluate the maximum conduction losses use the following equation :
$P = V_{to} \times I_{F(AV)} + rd \times I_{F}^{2}{}_{(RMS)}$

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	Tj = 25°C I_F = 0.5 A I_R = 1A Irr = 0.25A I_F = 1 A dI_F/dt =-50A/µs V_R =30V		35	 65	ns
I_{RM}	Maximum reverse recovery current	Tj = 125°C VR = 400V I_F =30A dI_F/dt = -240 A/µs dI_F/dt = -500 A/µs		 20	19	A
S factor	Softness factor	Tj = 125°C V_R = 400V I_F =30A dI_F/dt = -500 A/µs		0.40		-

TURN-ON SWITCHING

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
t_{fr}	Forward recovery time	Tj = 25°C I_F =30A, dI_F/dt = 240 A/µs measured at, 1.1 × $V_F$max			600	ns
V_{Fp}	Peak forward voltage	Tj = 25°C I_F =30A, dI_F/dt = 240 A/µs			12	V

Fig. 1: Conduction losses versus average current.

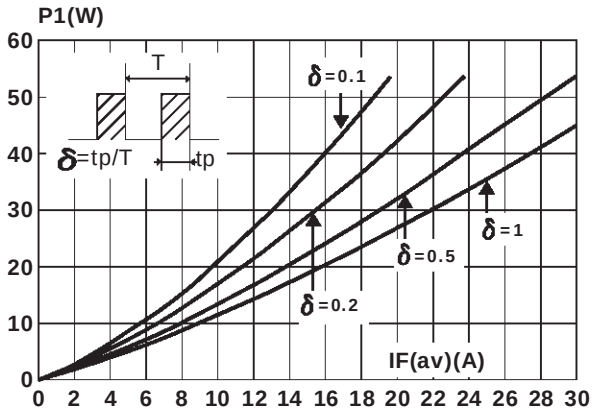


Fig. 2: Forward voltage drop versus forward current.

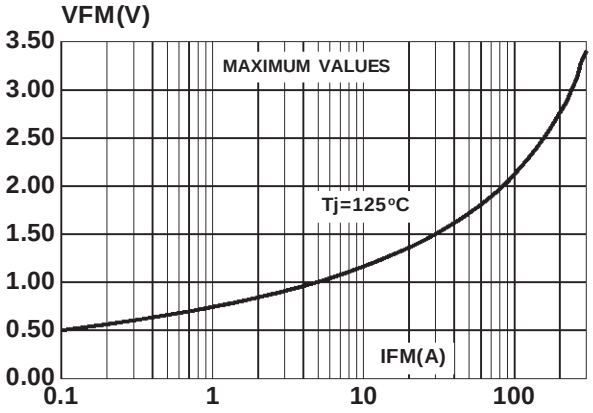


Fig. 3: Relative variation of thermal transient impedance junction to case versus pulse duration.

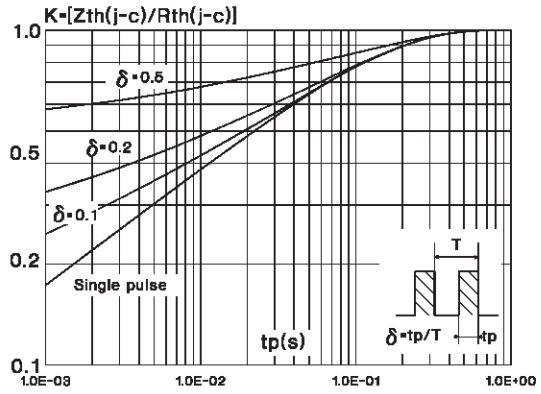


Fig. 4: Peak reverse recovery current versus dI_F/dt.

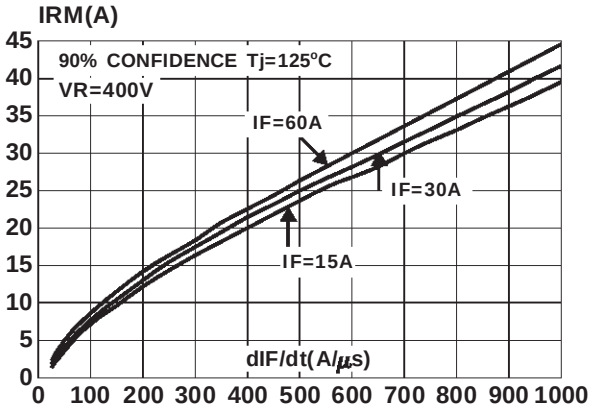


Fig. 5: Reverse recovery time versus dI_F/dt.

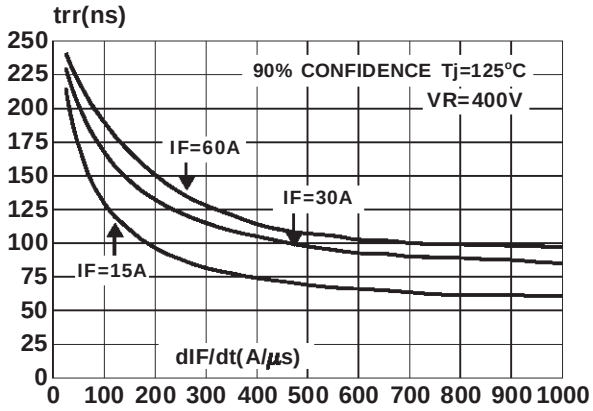


Fig. 6: Softness factor (tb/ta) versus dI_F/dt.

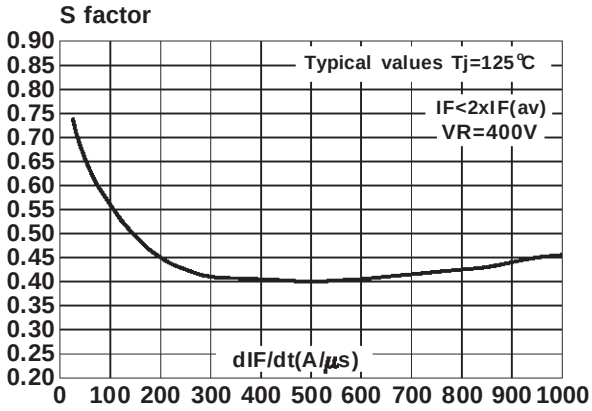


Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference Tj=125°C).

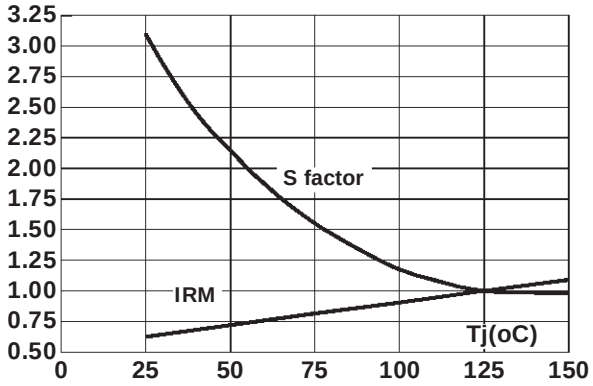


Fig. 8: Transient peak forward voltage versus dI_F/dt.

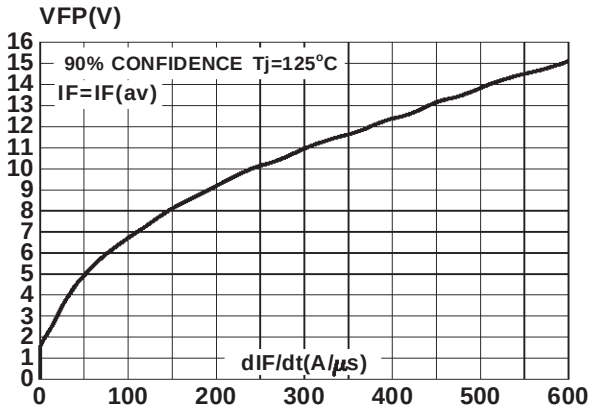
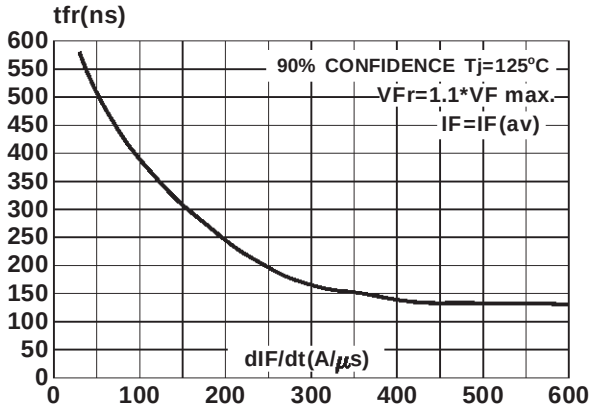


Fig. 9: Forward recovery time versus dI_F/dt.



APPLICATION DATA

The TURBOSWITCH is especially designed to provide the lowest overall power losses in any "FREEWHEEL Mode" application (Fig.A) considering both the diode and the companion transistor, thus optimizing the overall performance in the end application.
The way of calculating the power losses is given below:

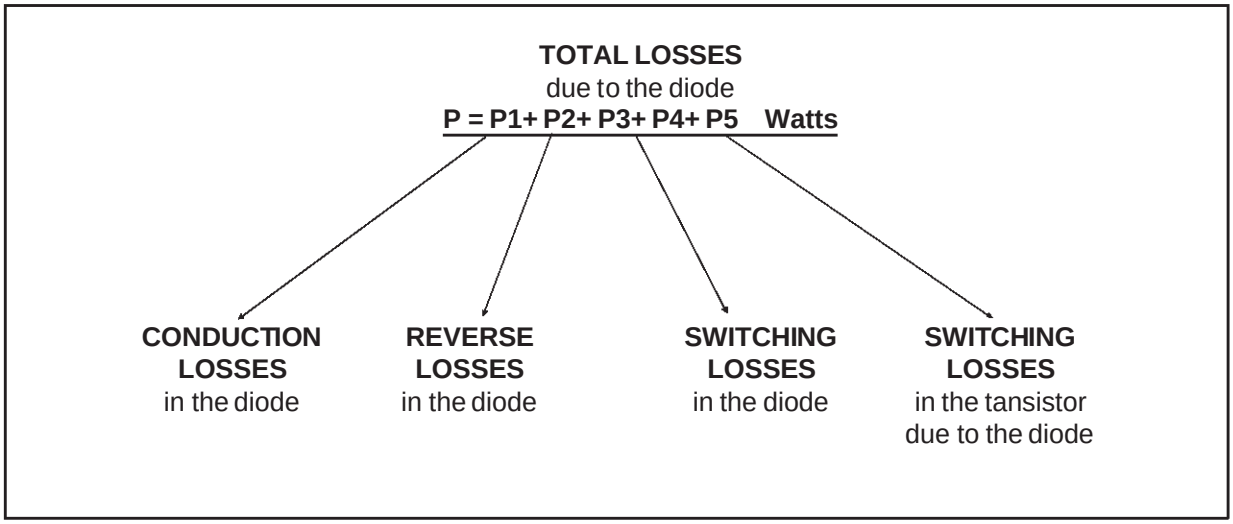
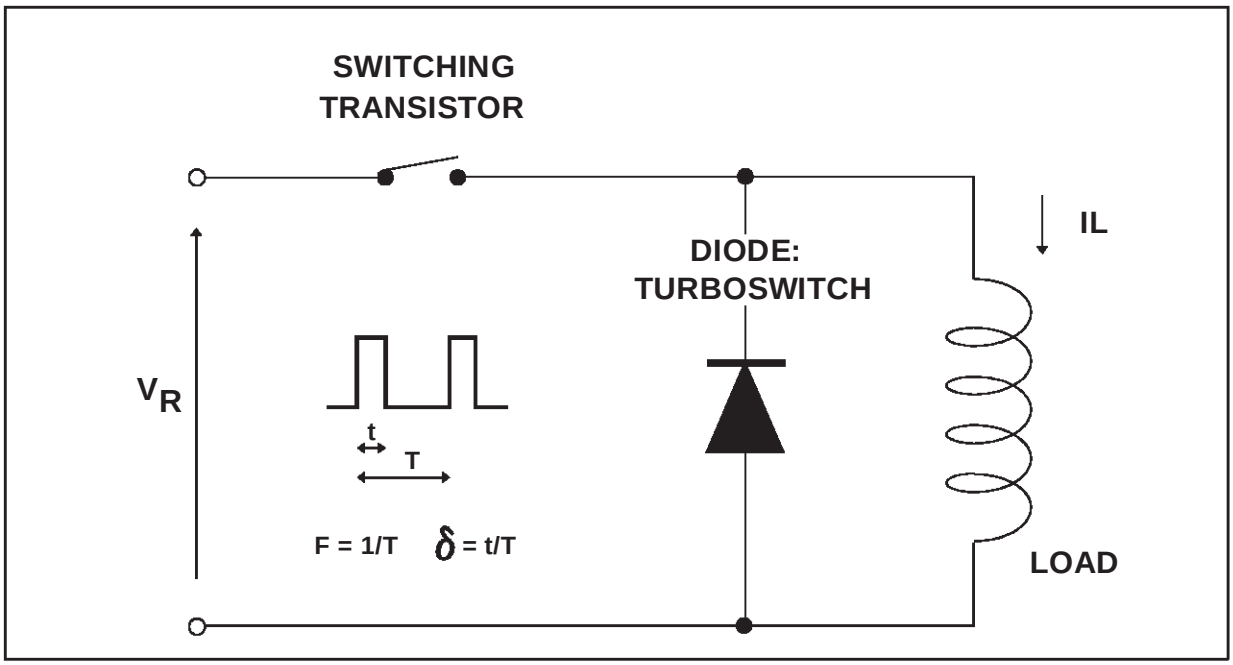
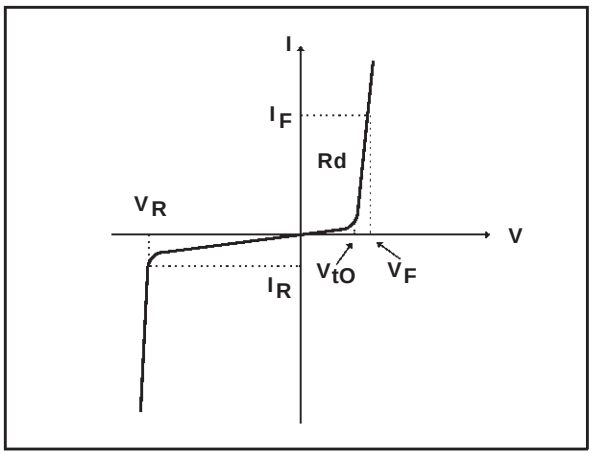


Fig. A : "FREEWHEEL" MODE.



APPLICATION DATA (Cont'd)

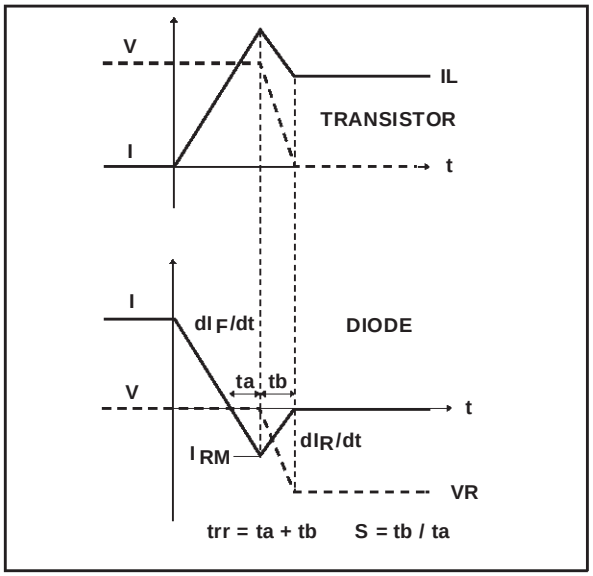
Fig. B: STATIC CHARACTERISTICS



Conduction losses:
$P1 = V_{t0} \cdot I_{F(AV)} + R_d \cdot I_F^2{}_{(RMS)}$

Reverse losses:
$P2 = V_R \cdot I_R \cdot (1 - \delta)$

Fig. C: TURN-OFF CHARACTERISTICS



Turn-on losses:
(in the transistor, due to the diode)

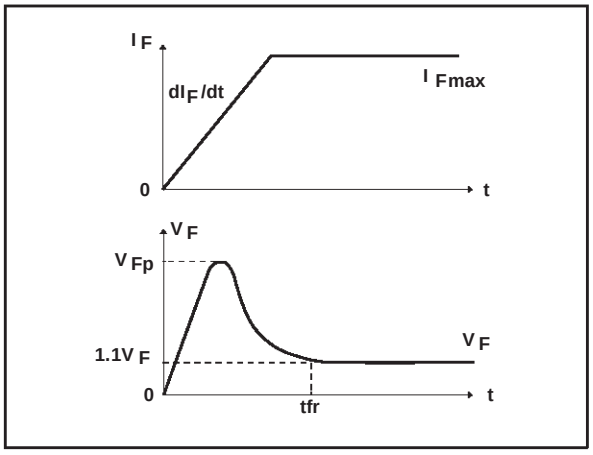
$$P5 = \frac{V_R \times I_{RM}{}^2 \times (3 + 2 \times S) \times F}{6 \; x \; dI_F/dt} + \frac{V_R \times I_{RM} \times I_L \times (S + 2) \times F}{2 \; x \; dI_F/dt}$$

Turn-off losses (in the diode):

$$P3 = \frac{V_R \times I_{RM}{}^2 \times S \times F}{6 \; x \; dI_F/dt}$$

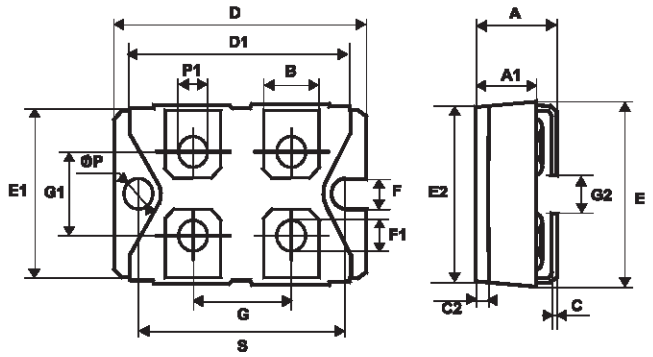
P3 and P5 are suitable for power MOSFET and IGBT

Fig. D: TURN-ON CHARACTERISTICS



Turn-on losses:
$P4 = 0.4 \, (V_{FP} - V_F) \cdot I_{Fmax} \cdot t_{fr} \cdot F$

PACKAGE MECHANICAL DATA
ISOTOP

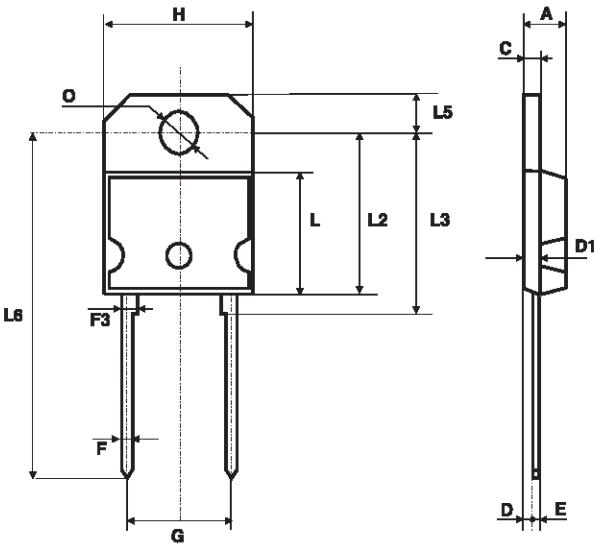


REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	11.80		12.20	0.465		0.480
A1	8.90		9.10	0.350		0.358
B	7.8		8.20	0.307		0.323
C	0.75		0.85	0.030		0.033
C2	1.95		2.05	0.077		0.081
D	37.80		38.20	1.488		1.504
D1	31.50		31.70	1.240		1.248
E	25.15		25.50	0.990		1.004
E1	23.85		24.15	0.939		0.951
E2		24.80			0.976	
G	14.90		15.10	0.587		0.594
G1	12.60		12.80	0.496		0.504
G2	3.50		4.30	0.138		0.169
F	4.10		4.30	0.161		0.169
F1	4.60		5.00	0.181		0.197
P	4.00		4.30	0.157		0.69
P1	4.00		4.40	0.157		0.173
S	30.10		30.30	1.185		1.193

Cooling method : by conduction (C)

PACKAGE MECHANICAL DATA

SOD93



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.70		4.90	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.50			0.098	
D1		1.27			0.050	
E	0.50		0.78	0.020		0.031
F	1.10		1.30	0.043		0.051
F3		1.75			0.069	
G	10.80		11.10	0.425		0.437
H	14.70		15.20	0.578		0.598
L			12.20			0.480
L2			16.20			0.638
L3		18.0			0.709	
L5	3.95		4.15	0.156		0.163
L6		31.00			1.220	
O	4.00		4.10	0.157		0.161

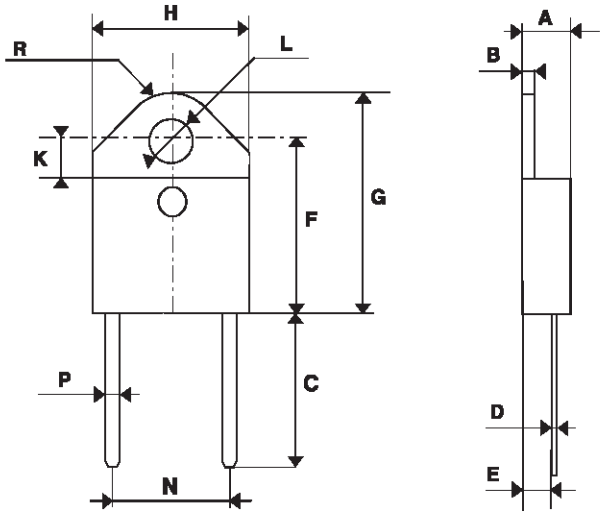
Cooling method : by conduction (C)

Recommended torque value : 0.8 m.N

Maximum torque value : 1m.N

PACKAGE MECHANICAL DATA

DOP3I



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	1.45	1.55	0.057	0.061
C	14.35	15.60	0.565	0.614
D	0.5	0.7	0.020	0.028
E	2.7	2.9	0.106	0.114
F	15.8	16.5	0.622	0.650
G	20.4	21.1	0.815	0.831
H	15.1	15.5	0.594	0.610
K	3.4	3.65	0.134	0.144
L	4.08	4.17	0.161	0.164
N	10.8	11.3	0.425	0.444
P	1.20	1.40	0.047	0.055
R	4.60 typ.		0.181 typ.	

Cooling method : by conduction (C)

Recommended torque value : 0.8 m.N

Maximum torque value : 1m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTA6006P	STTA6006P	SOD93	3.79g	30	Tube
STTA6006PI	STTA6006PI	DOP3I	4.52g	30	Tube
STTA6006TV1	STTA6006TV1	ISOTOP	27g without screws	10	Tube
STTA6006TV2	STTA006TV2	ISOTOP		10	Tube

■ Epoxy meets UL94,V0

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